

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE ( $\pi$ -MOSII-5)

# 2SK1643

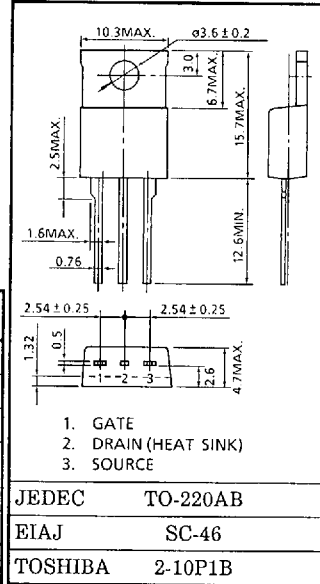
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS.  
DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS.

INDUSTRIAL APPLICATIONS  
Unit in mm

- Low Drain-Source ON Resistance :  $R_{DS(ON)} = 2.5\Omega$  (Typ.)
- High Forward Transfer Admittance :  $|Y_{fs}| = 2.0S$  (Typ.)
- Low Leakage Current :  $I_{DSS} = 300\mu A$  (Max.) @  $V_{DS} = 720V$
- Enhancement-Mode :  $V_{th} = 1.5 \sim 3.5V$  @  $V_{DS} = 10V, I_D = 1mA$

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$V_{DSS}$	900	V
Drain-Gate Voltage ( $R_{GS} = 20k\Omega$ )	$V_{DGR}$	900	V
Gate-Source Voltage	$V_{GSS}$	$\pm 30$	V
Drain Current	DC	$I_D$	5
	Pulse	$I_{DP}$	15
Drain Power Dissipation ( $T_c = 25^\circ C$ )	$P_D$	125	W
Channel Temperature	$T_{ch}$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	$-55 \sim 150$	$^\circ C$



JEDEC	TO-220AB
EIAJ	SC-46
TOSHIBA	2-10P1B

Weight : 2.0g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	1.0	$^\circ C / W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	83.3	$^\circ C / W$

THIS TRANSISTOR IS AN ELECTROSTATIC SENSITIVE DEVICE. PLEASE HANDLE WITH CAUTION.

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## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		$I_{GSS}$	$V_{GS} = \pm 25V, V_{DS} = 0V$	—	—	$\pm 100$	nA
Drain Cut-off Current		$I_{DSS}$	$V_{DS} = 720V, V_{GS} = 0V$	—	—	300	$\mu A$
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 10mA, V_{GS} = 0V$	900	—	—	V
Gate Threshold Voltage		$V_{th}$	$V_{DS} = 10V, I_D = 1mA$	1.5	—	3.5	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 2A$	—	2.5	2.8	$\Omega$
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 20V, I_D = 2A$	1.0	2.0	—	S
Input Capacitance		$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	—	700	1000	pF
Reverse Transfer Capacitance		$C_{rss}$		—	55	90	
Output Capacitance		$C_{oss}$		—	100	150	
Switching Time	Rise Time	$t_r$	<p><math>V_{GS} = 10V, I_D = 2A, V_{OUT}</math>  <math>R_L = 200\Omega</math>  <math>V_{IN} : t_r, t_f &lt; 5ns, V_{DD} = 400V</math>  <math>Duty \leq 1\%, t_w = 10\mu s</math></p>	—	18	35	ns
	Turn-on Time	$t_{on}$		—	30	60	
	Fall Time	$t_f$		—	12	25	
	Turn-off Time	$t_{off}$		—	70	140	
Total Gate Charge (Gate-Source Plus Gate-Drain)		$Q_g$	$V_{DD} = 400V, V_{GS} = 10V, I_D = 4A$	—	60	120	nC
Gate-Source Charge		$Q_{gs}$		—	35	—	
Gate-Drain ("Miller") Charge		$Q_{gd}$		—	25	—	

## SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	$I_{DR}$	—	—	—	5	A
Pulse Drain Reverse Current	$I_{DRP}$	—	—	—	15	A
Diode Forward Voltage	$V_{DSF}$	$I_{DR} = 4A, V_{GS} = 0V$	—	—	-1.9	V
Reverse Recovery Time	$t_{rr}$	$I_{DR} = 4A, V_{GS} = 0V$	—	1000	—	ns
Reverse Recovered Charge	$Q_{rr}$	$dI_{DR} / dt = 100A / \mu s$	—	0.13	—	$\mu C$

